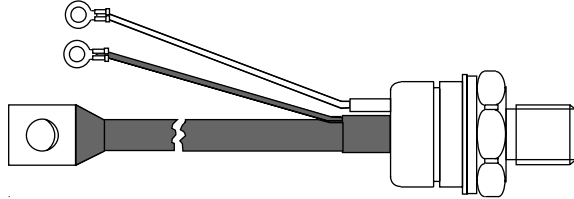


Phase Control Thyristors (Stud Version), 180 A



TO-209AB (TO-93)

FEATURES

- Hermetic glass-metal seal
- International standard case TO-209AB (TO-93)
- RoHS compliant
- Lead (Pb)-free
- Designed and qualified for industrial level



RoHS
COMPLIANT

PRODUCT SUMMARY

$I_{T(AV)}$	180 A
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TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		180	A
	T_C	80	°C
$I_{T(RMS)}$		285	A
I_{TSM}	50 Hz	3800	
	60 Hz	4000	
I^2t	50 Hz	72	kA ² s
	60 Hz	66	
V_{DRM}/V_{RRM}		400 to 1000	V
t_q	Typical	100	µs
T_J		- 40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

PART NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
180/181RKI	40	400	500	30
	80	800	900	
	100	1000	1100	

180RKI...PbF /181RKI...PbF Series



Vishay High Power Products Phase Control Thyristors
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ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current at case temperature	$I_{T(AV)}$	180° conduction, half sine wave		180	A
				80	°C
Maximum RMS on-state current	I_{RMS}	DC at 79 °C case temperature		285	
Maximum peak, one-cycle non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reapplied	3800	A
		t = 8.3 ms		4000	
		t = 10 ms	100 % V_{RRM} reapplied	3500	
		t = 8.3 ms		3660	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied	72	kA ² s
		t = 8.3 ms		66	
		t = 10 ms	100 % V_{RRM} reapplied	61	
		t = 8.3 ms		56	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied		720	kA ² √s
Low level value of threshold voltage	$V_{T(TO)1}$	$(16.7\% \times \pi \times I_{T(AV)}) < I < \pi \times I_{T(AV)}$, $T_J = T_J$ maximum		0.83	V
High level value of threshold voltage	$V_{T(TO)2}$	$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ maximum		0.89	
Low level value of on-state slope resistance	r_{t1}	$(16.7\% \times \pi \times I_{T(AV)}) < I < \pi \times I_{T(AV)}$, $T_J = T_J$ maximum		0.92	mΩ
High level value of on-state slope resistance	r_{t2}	$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ maximum		0.81	
Maximum on-state voltage	V_{TM}	$I_{pk} = 570$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sine pulse		1.35	V
Maximum holding current	I_H	$T_J = 25$ °C, anode supply 12 V resistive load		600	mA
Typical latching current	I_L			1000	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	di/dt	Gate drive 20 V, 20 Ω, $t_r \leq 1$ μs $T_J = T_J$ maximum, anode voltage $\leq 80\%$ V_{DRM}		300	A/μs
Typical delay time	t_d	Gate current 1 A, $di_g/dt = 1$ A/μs $V_d = 0.67\%$ V_{DRM} , $T_J = 25$ °C		1.0	μs
Typical turn-off time	t_q	$I_{TM} = 50$ A, $T_J = T_J$ maximum, $di/dt = 10$ A/μs, $V_R = 100$ V $dV/dt = 20$ V/μs		100	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}		500	V/μs
Maximum peak reverse and off-state leakage current	I_{RRM} , I_{DRM}	$T_J = T_J$ maximum rated V_{DRM}/V_{RRM} applied		30	mA



180RKI...PbF /181RKI...PbF Series

Phase Control Thyristors Vishay High Power Products
(Stud Version), 180 A

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
				TYP.	MAX.	
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms		10		W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum, $f = 50$ Hz, $d\% = 50$		2.0		
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms		3.0		A
Maximum peak positive gate voltage	$+V_{GM}$			20		V
Maximum peak negative gate voltage	$-V_{GM}$			5.0		
DC gate current required to trigger	I_{GT}	$T_J = -40$ °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	130	-	mA
		$T_J = 25$ °C		65	150	
		$T_J = 125$ °C		35	-	
DC gate voltage required to trigger	V_{GT}	$T_J = -40$ °C		2.0	-	V
		$T_J = 25$ °C		1.2	2.5	
		$T_J = 125$ °C		0.9	-	
DC gate current not to trigger	I_{GD}	$T_J = T_J$ maximum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V_{DRM} anode to cathode applied	10		mA
DC gate voltage not to trigger	V_{GD}			0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction temperature range	T_J		- 40 to 125	°C
Maximum storage temperature range	T_{Stg}		- 40 to 150	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	0.15	K/W
Maximum thermal resistance, junction to ambient	R_{thCS}	Mounting surface, smooth, flat and greased	0.04	
Mounting force, ± 10 %		Non-lubricated threads	31 (275)	Nm (lbf · in)
		Lubricated threads	24.5 (210)	
Approximate weight			280	g
Case style		See dimensions - link at the end of datasheet	TO-209AB (TO-93)	

ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.050	0.032	$T_J = T_J$ maximum	K/W
120°	0.063	0.059		
90°	0.080	0.082		
60°	0.118	0.124		
30°	0.225	0.228		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

180RKI...PbF /181RKI...PbF Series



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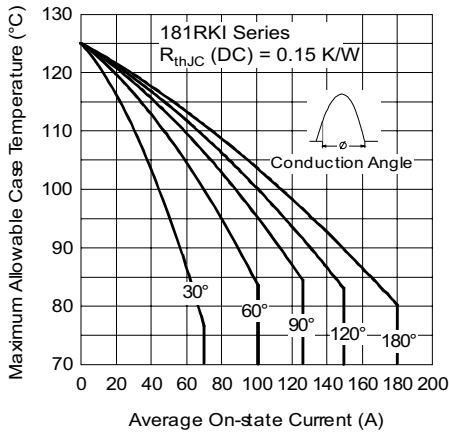


Fig. 1 - Current Ratings Characteristics

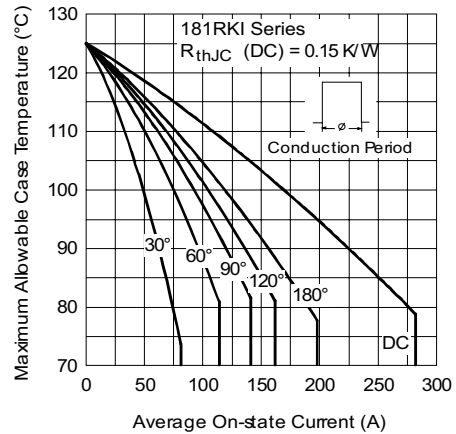


Fig. 2 - Current Ratings Characteristics

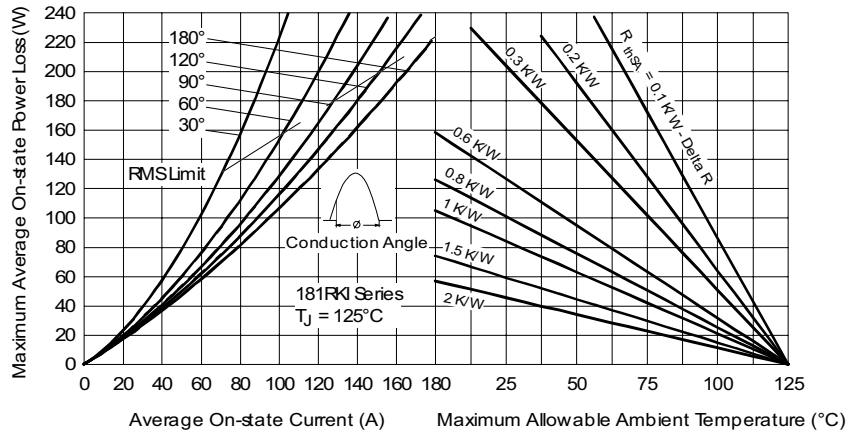


Fig. 3 - On-State Power Loss Characteristics

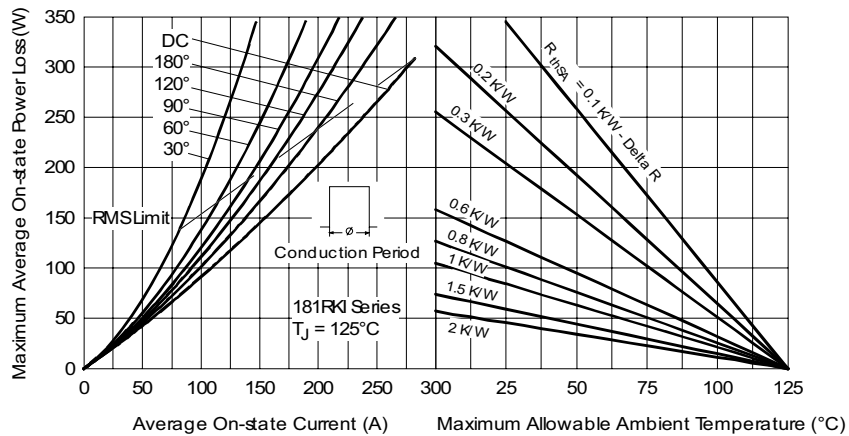


Fig. 4 - On-State Power Loss Characteristics



180RKI...PbF /181RKI...PbF Series

Phase Control Thyristors (Stud Version), 180 A Vishay High Power Products

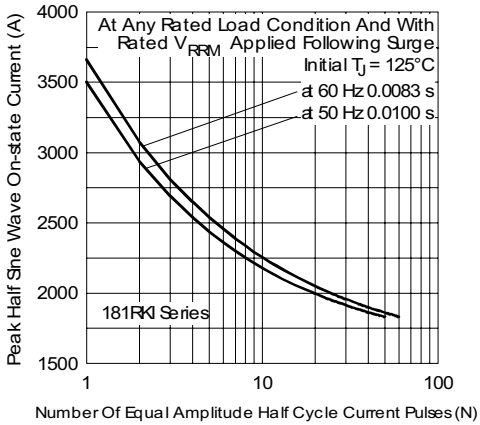


Fig. 5 - Maximum Non-Repetitive Surge Current

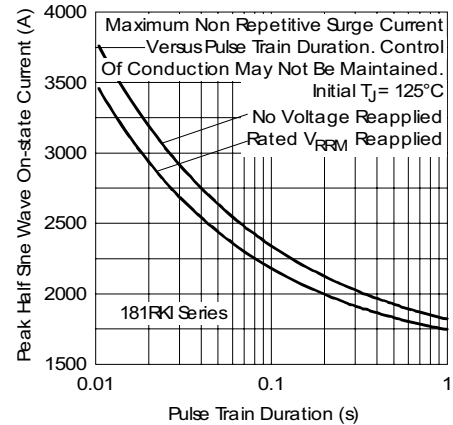


Fig. 6 - Maximum Non-Repetitive Surge Current

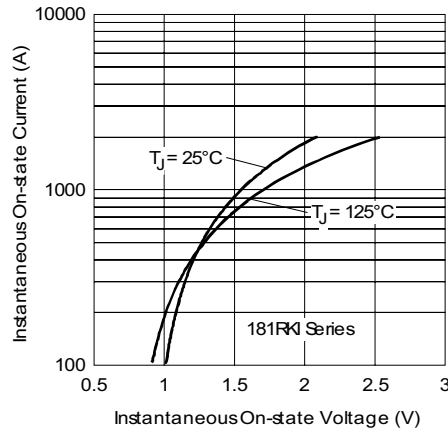


Fig. 7 - On-State Voltage Drop Characteristics

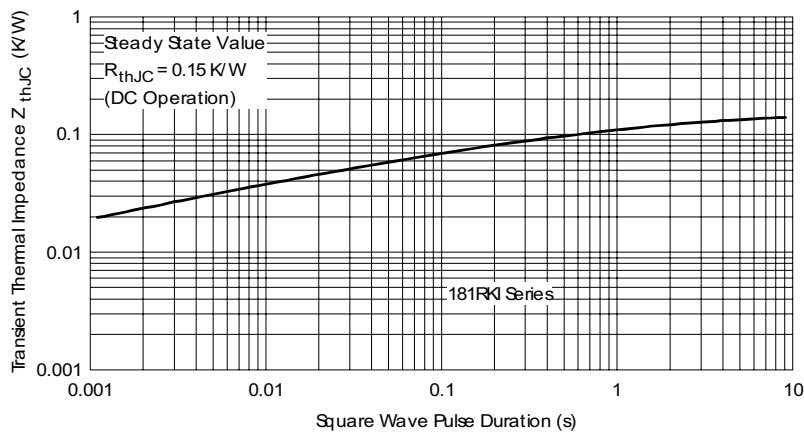


Fig. 8 - Thermal impedance Z_{thJC} Characteristics

180RKI...PbF /181RKI...PbF Series



Vishay High Power Products Phase Control Thyristors
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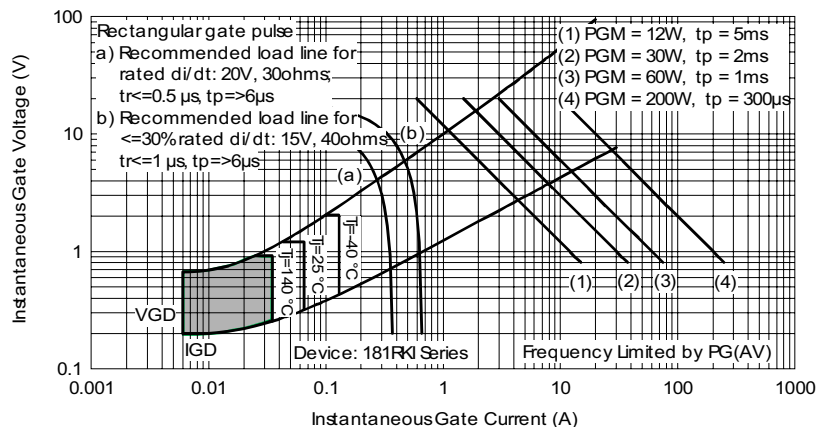


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	18	1	RKI	100	PbF
	①	②	③	④	⑤
	1	-	$I_{T(AV)}$ rated average output current (rounded/10)		
	2	-	0 = Eyelet terminals (gate and auxiliary cathode leads) 1 = Fast-on terminals (gate and auxiliary cathode leads)		
	3	-	Thyristor		
	4	-	Voltage code x 10 = V_{RRM} (see Voltage Ratings table)		
	5	-	Lead (Pb)-free		

LINKS TO RELATED DOCUMENTS

Dimensions	http://www.vishay.com/doc?95077
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Notice

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TO-209AB (TO-93)

DIMENSIONS in millimeters (inches)

Case Style TO-209AB (TO-93)

